

SuperMOS – SOT-23 -20V BV_{DSS} , 82m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The NCE2301-ES is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product NCE2301-ES is Pb-free.

2. Features

- -20V, $R_{DS(ON)}=82m\Omega(TYP.) @V_{GS}=-4.5V$
 $R_{DS(ON)}=118m\Omega(TYP.) @V_{GS}=-2.5V$
 $R_{DS(ON)}=180m\Omega(TYP.) @V_{GS}=-1.8V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

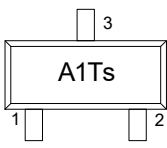
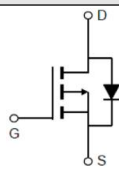
4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
NCE2301-ES	SOT-23	2301	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

NCE2301-ES

Rev-1.2

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	-2	A
	$T_A = 100^\circ\text{C}$		-1.3	
Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	0.8	W
Pulsed Drain Current		I_{DM}	-8	A
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ($t \leq 10\text{s}$)	$R_{\theta JA}$		156	$^\circ\text{C/W}$

NCE2301-ES

Rev-1.2

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.62	-1.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-2A		82	95	mΩ
		V _{GS} =-2.5A, I _D =-1.5A		118	138	
		V _{GS} =-1.8V, I _D =-1A		180	210	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-10V f=1MHz		185		pF
Output Capacitance	C _{OSS}			35		
Reverse Transfer Capacitance	C _{RSS}			25		
Total Gate Charge	Q _G	V _{GS} =-4.5V, V _{DS} =-10V I _D =-2A		2.2		nC
Gate-to-Source Charge	Q _{GS}			0.5		
Gate-to-Drain Charge	Q _{GD}			0.5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-4.5V, V _{DS} =-10V R _L =5Ω, R _G =3Ω		10		ns
Rise Time	t _r			30		
Turn-Off Delay Time	t _{d(OFF)}			62		
Fall Time	t _f			50		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-2A			-1.5	V

7. Typical Characteristics

Figure 1: Output Characteristics

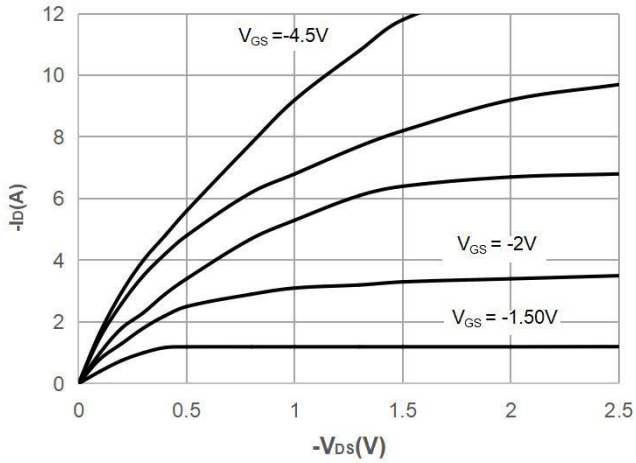


Figure 2: Typical Transfer Characteristics

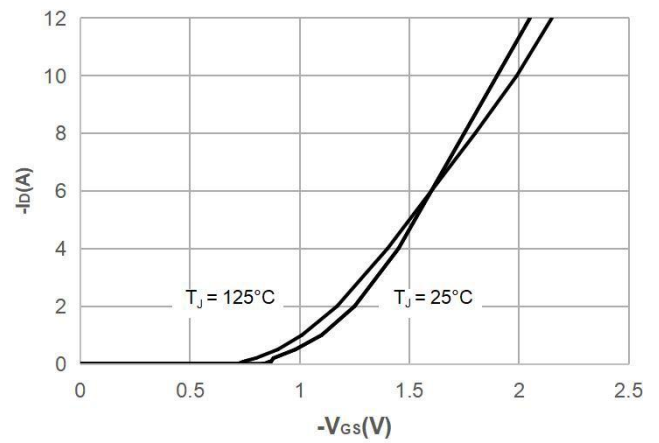


Figure 3: On-resistance vs. Drain Current

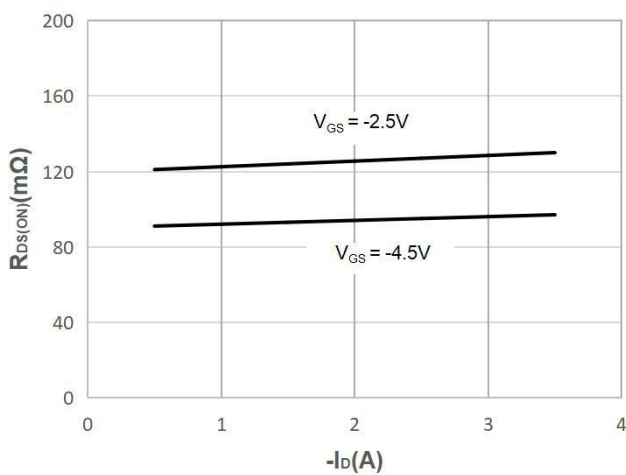


Figure 4: Body Diode Characteristics

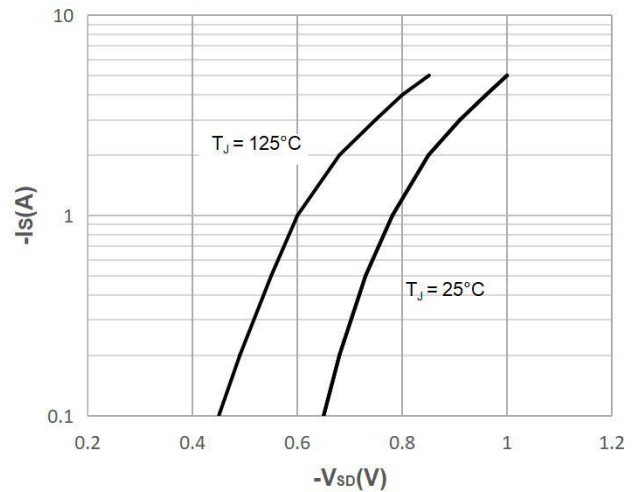


Figure 5: Gate Charge Characteristics

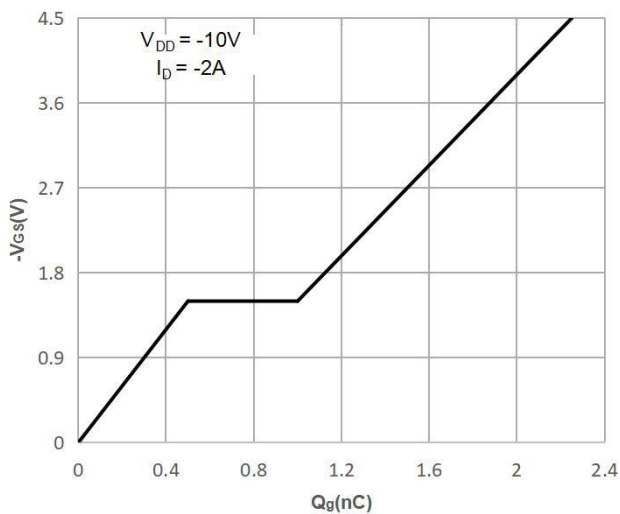


Figure 6: Capacitance Characteristics

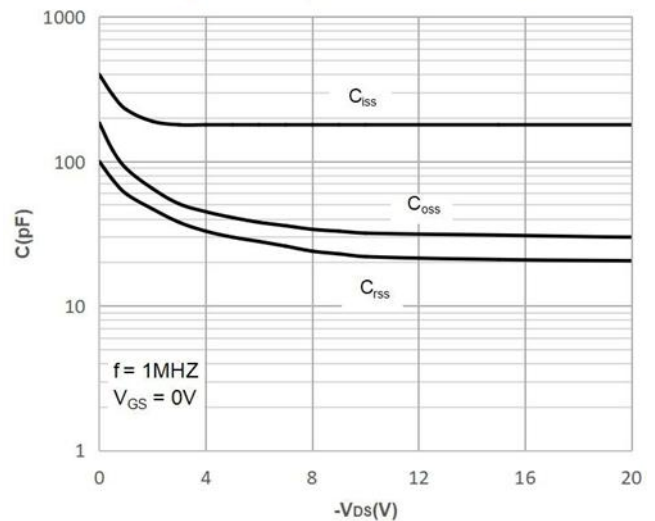


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

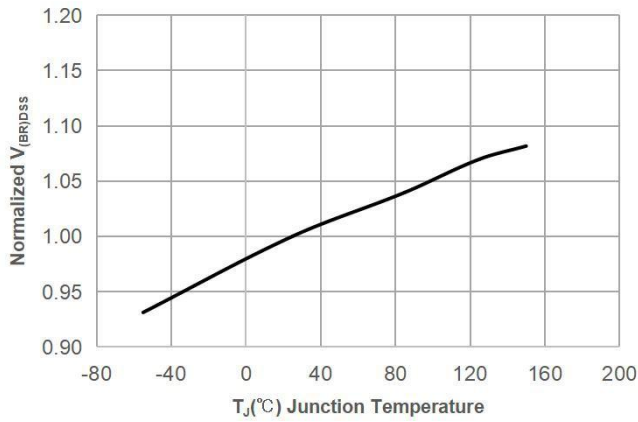


Figure 8: Normalized on Resistance vs. Junction Temperature

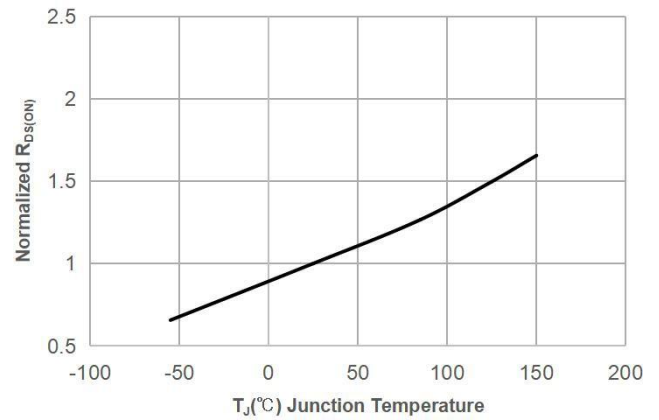


Figure 9: Maximum Safe Operating Area

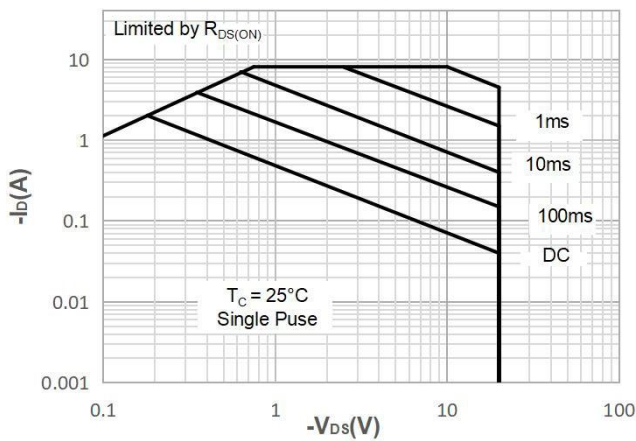


Figure 10: Maximum Continuous Driant Current vs. Case Temperature

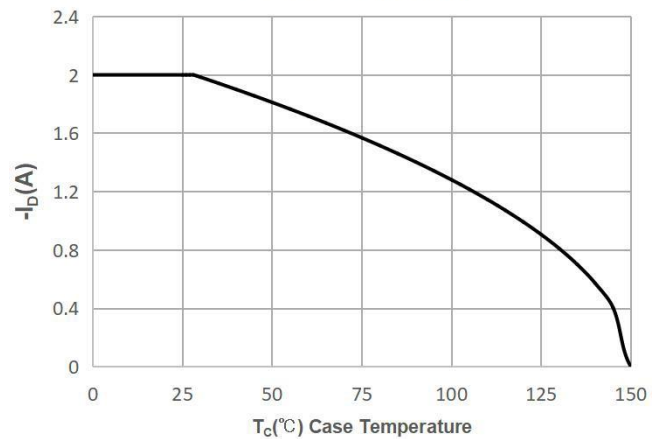


Figure 11: Normalized Maximum Transient Thermal Impedance

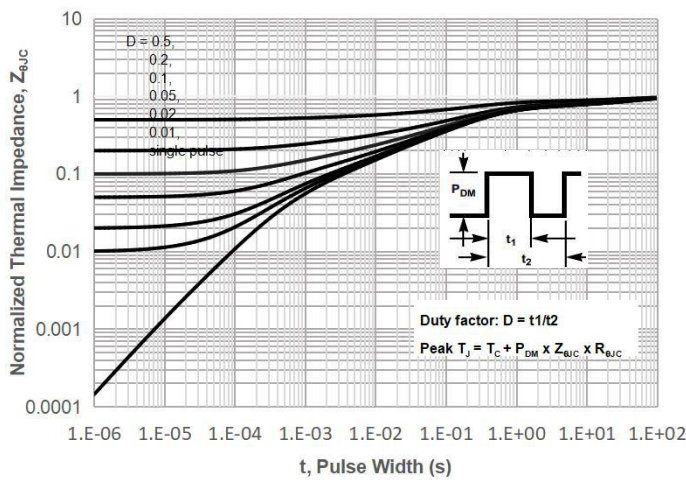
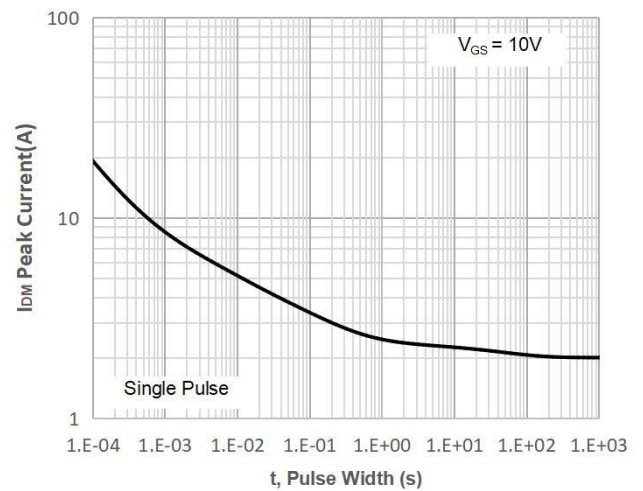
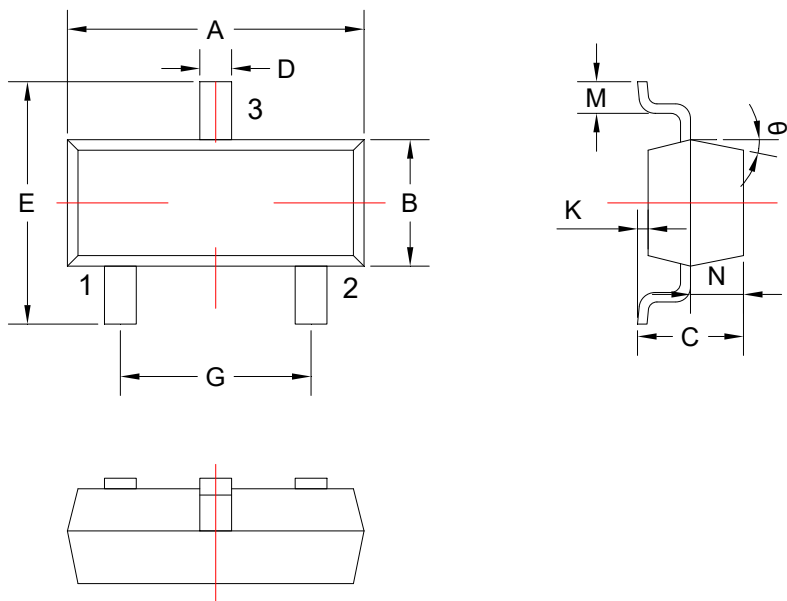


Figure 12: Peak Current Capacity



8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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